

Medium Power Transistor (-32V, -1A)

2SB1132 / 2SA1515S / 2SB1237

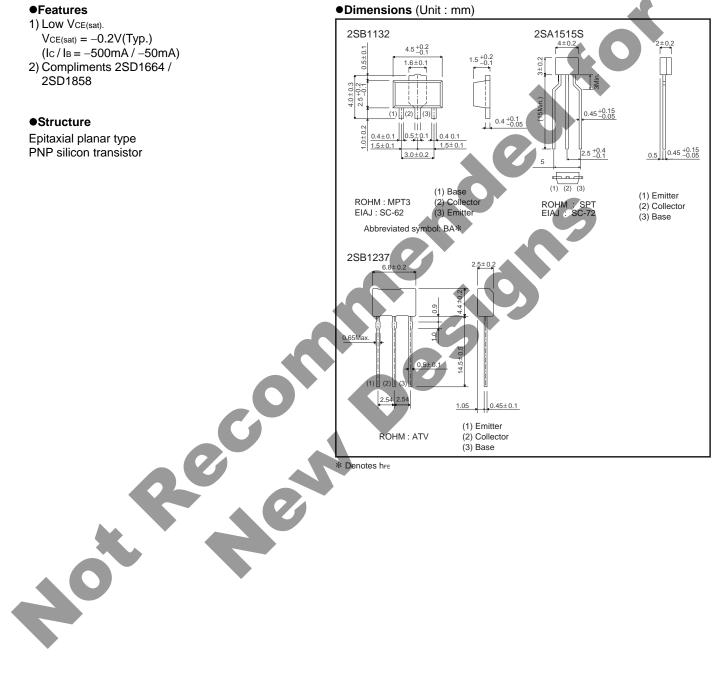
Features

1) Low VCE(sat). $V_{CE(sat)} = -0.2V(Typ.)$ (Ic/IB = -500mA/-50mA)

2) Compliments 2SD1664 / 2SD1858

Structure

Epitaxial planar type PNP silicon transistor



● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		Vсво	-40	V
Collector-emitter voltage		Vceo	-32	V
Emitter-base voltage		VEBO	- 5	V
Collector current		l-	-1	A(DC)
		lc	-2	A(Pulse) *1
Collector power dissipation	2SB1132	D	0.5	
			2	*2 W
	2SA1515S	Pc	0.3	VV
	2SB1237		1	*3
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C

^{*1} Single pulse, Pw=100ms

●Electrical characteristics (Ta=25°C)

				-2		A(Pulse	*) *1	
	2SB1132			0.5				
Collector power	-			2		W	*2	
	2SA1515S	Pc		0.3		VV		
	2SB1237		1					
Junction temperature Tj			150		င			
Storage temperature Tstg		_	-55 to +150		°C			
*3 Printed circuit be				9 10011111	or largor.			
Pa	arameter		Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage			Cyllibol	IVIIII.	.,,,,,	Wich.	Unit	Conditions
Collector-base b	reakdown vo	oltage	ВУсво	-40	-		V	Ic=-50µA
			,					
Collector-base b Collector-emitter Emitter-base bre	breakdown	voltage	ВУсво	-40	-	-	V	lc=-50μA
Collector-emitter Emitter-base bre	breakdown eakdown volt	voltage	BVcB0 BVcE0	-40 -32	-	-	V	Ic=-50μA Ic=-1mA
Collector-emitter	r breakdown eakdown volt current	voltage	BVCBO BVCEO BVEBO	-40 -32 -5	- -		V	Ic= -50μA Ic= -1mA Iε= -50μA
Collector-emitter Emitter-base bre Collector cutoff of	breakdown eakdown volt current rrent	voltage age	BVCBO BVCEO BVEBO ICBO	-40 -32 -5 -	- - -	- - - -0.5	V V V	Ic=-50μA Ic=-1mA Iε=-50μA VcB=-20V
Collector-emitter Emitter-base bre Collector cutoff cu	breakdown volt current rrent saturation v	voltage age	BVCBO BVCEO BVEBO ICBO ICBO VCE(sat)	-40 -32 -5 -	- - - -	- - -0.5 -0.5	V V V µA µA	Ic= -50μA Ic= -1mA IE= -50μA VcB= -20V VEB= -4V Ic/IB= -500mA/=50mA *
Collector-emitter Emitter-base bre Collector cutoff of Emitter cutoff cu Collector-emitter DC current	breakdown volt current rrent saturation v	voltage age voltage 2, 2SB1237	BVCBO BVEBO ICBO IEBO	-40 -32 -5 -	- - - -	- - -0.5 -0.5	V V V μΑ μΑ V	$I_{C} = -50 \mu A$ $I_{C} = -1 mA$ $I_{E} = -50 \mu A$ $V_{CB} = -20 V$ $V_{EB} = -4 V$ $I_{C}/I_{B} = -500 mA/-50 mA$ *
Collector-emitter Emitter-base bre Collector cutoff of Emitter cutoff cut Collector-emitter	eakdown volt current rrent saturation v 2SB1132 2SA1515	voltage age voltage 2, 2SB1237	BVCBO BVCEO BVEBO ICBO ICBO VCE(sat)	-40 -32 -5 - - - - 120	- - - -	- - -0.5 -0.5 -0.5 390	V V µА µА V	Ic= -50μA Ic= -1mA IE= -50μA VcB= -20V VEB= -4V Ic/IB= -500mA/-50mA *

^{*} Measured using pulse current.

●Packaging specifications and hFE

		Package		Taping	
		Code	T100	TP	TU2
Туре	hfE	Basic ordering unit (pieces)	1000	5000	2500
2SB1132	QR		0	-	_
2SA1515S	QR		_	0	_
2SB1237	QR		-	_	0

her values are classified as follows:

Item	Q	R		
hfe	120 to 270	180 to 390		

^{\$2} When mounted on a 40×40×0.7 mm ceramic board.

•Electrical characteristics curves

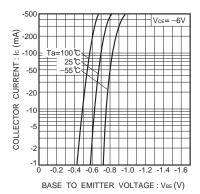


Fig.1 Grounded emitter propagation characteristics

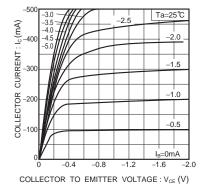


Fig.2 Grounded emitter output characteristics

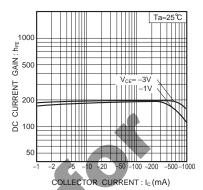


Fig.3 DC current gain vs. collector current(I)

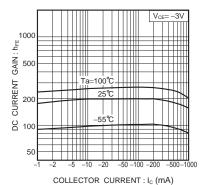


Fig.4 DC current gain vs. collector current(II)

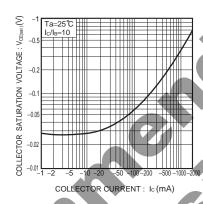


Fig.5 Collector-emitter saturation voltage vs. collector current

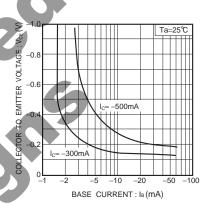


Fig.6 Collector-emitter saturation voltage vs. base current

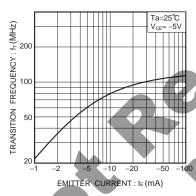


Fig.7 Gain bandwidth product vs. emitter current

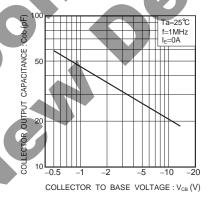


Fig.8 Collector output capacitance vs.collector-base voltage

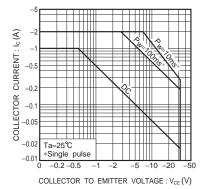


Fig.9 Safe operation area (2SB1132)

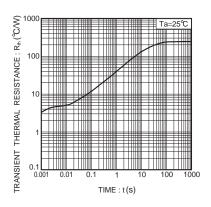


Fig.10 Transient thermal resistance (2SB1132)

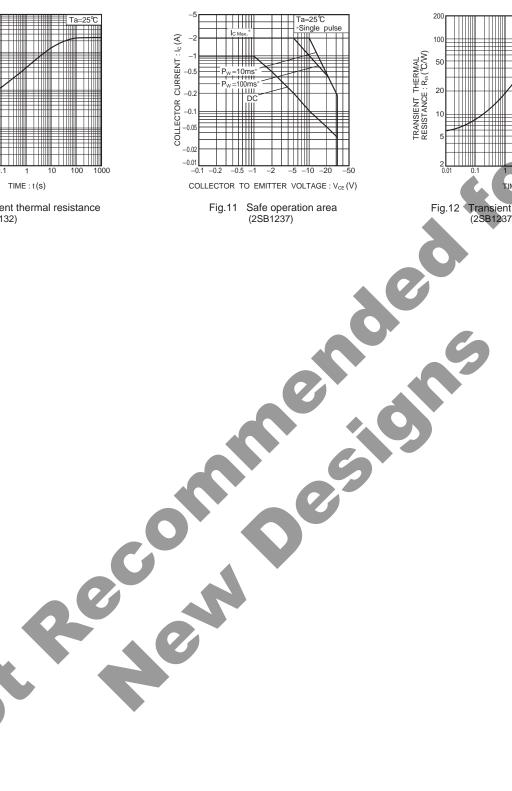


Fig.11 Safe operation area

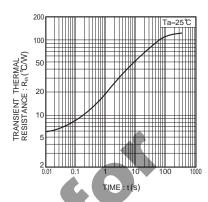


Fig.12 Transient thermal resistance (2SB1237)

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